

Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V	
V _{in}	DC Input Voltage		-0.5 to +7.0	V
V _{out}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current		±20	mA
I _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GN	ND Pins	± 50	mA
P _D	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-55	+ 125	°C

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	٦	Γ _A = 25°(С	T _A = -55	to +125°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage (Figure 5)		3.0 4.5 5.5			2.20 3.15 3.85		2.20 3.15 3.85	V
V _{T-}	Negative Threshold Voltage (Figure 5)		3.0 4.5 5.5	0.9 1.35 1.65			0.90 1.35 1.65		V
V _H	Hysteresis Voltage (Figure 5)		3.0 4.5 5.5	0.30 0.40 0.50		1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = - 4 \text{ mA} \\ I_{OH} = - 8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0 0 0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 4 \text{ mA} \\ I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μА
Icc	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			2.0		20.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

				Т	A = 25°	С	T _A = -55 t	to +125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		7.6 10.1	11.9 15.4	1.0 1.0	14.0 17.5	ns
	AUIBIOT	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		4.9 6.4	7.7 9.7	1.0 1.0	9.0 11.0	
C _{in}	Maximum Input Capacitance				4	10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 1)	16	pF

C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
 Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 5.0 V)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC132D	SOIC-14	55 Units / Rail
MC74VHC132DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74VHC132DR2	SOIC-14	2500 Tape & Reel
MC74VHC132DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74VHC132DTR2	TSSOP-14*	2500 Tape & Reel
M74VHC132DTR2G	TSSOP-14*	2500 Tape & Reel
MC74VHC132MEL	SOEIAJ-14	2000 Tape & Reel
MC74VHC132MELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

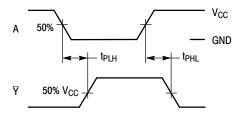


Figure 3. Switching Waveforms

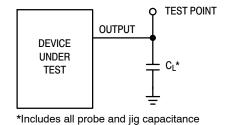
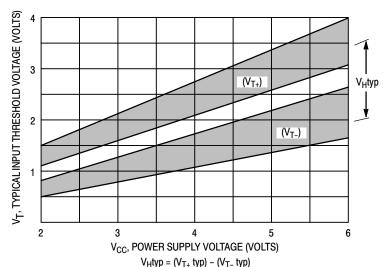


Figure 4. Test Circuit



 $V_H typ = (V_{T_+} typ) - (V_{T_-} typ)$ Figure 5. Typical Input Threshold, V_{T_+}, V_{T_-} versus Power Supply Voltage

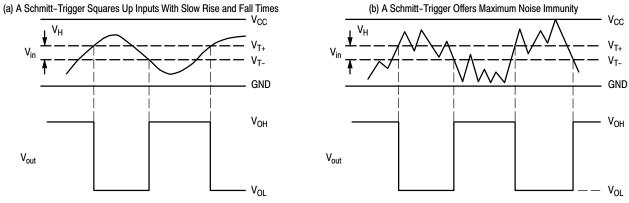


Figure 6. Typical Schmitt-Trigger Applications

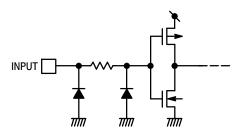
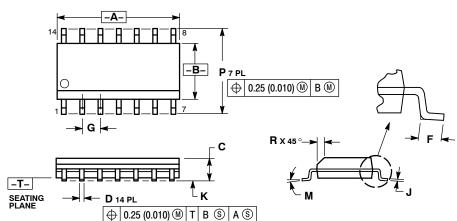


Figure 7. Input Equivalent Circuit

PACKAGE DIMENSIONS

SOIC-14 CASE 751A-03 **ISSUE J**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

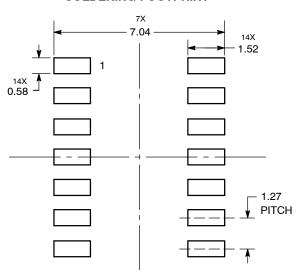
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7 °	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

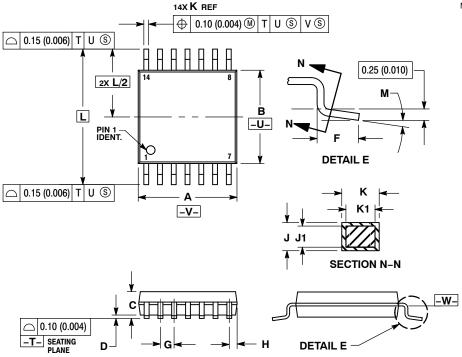


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE B**



NOTES:

- DTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

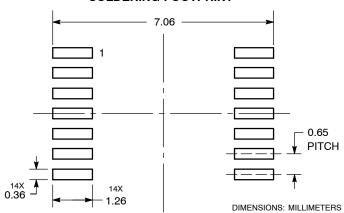
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
М	0 °	8 °	0 °	8 °	

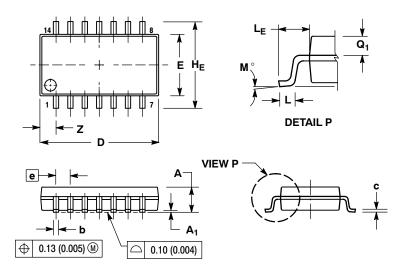
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 **ISSUE B**



NOTES:

- 1. DIMENUL. Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
- MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (USDO) FERTISIES

 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX		
Α		2.05		0.081		
A ₁	0.05	0.20	0.002	0.008		
b	0.35	0.50	0.014	0.020		
С	0.10	0.20	0.004	0.008		
D	9.90	10.50	0.390	0.413		
Е	5.10	5.45	0.201	0.215		
е	1.27 BSC		0.050	BSC		
HE	7.40	8.20	0.291	0.323		
L	0.50	0.85	0.020	0.033		
LΕ	1.10	1.50	0.043	0.059		
M	0 °	10°	0 °	10°		
Q ₁	0.70	0.90	0.028	0.035		
Z		1.42		0.056		

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